

Fig. 1

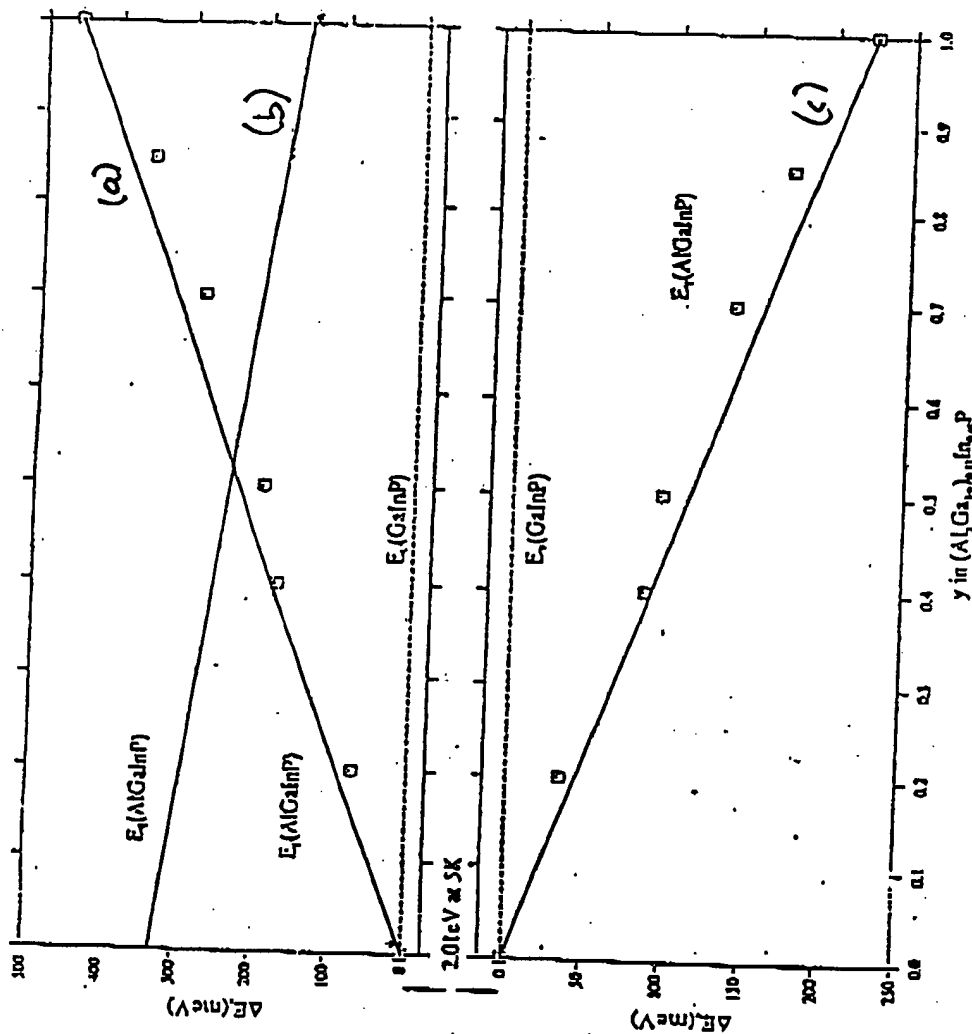


Fig. 1

A diagram of the variation of the $G_{0.52}In_{0.48}P/(AlGa)InP$ heterobarrier height (meV) as a function of aluminium mole fraction in the quaternary alloy assuming a 70:30 band offset ratio.

FIG. 2

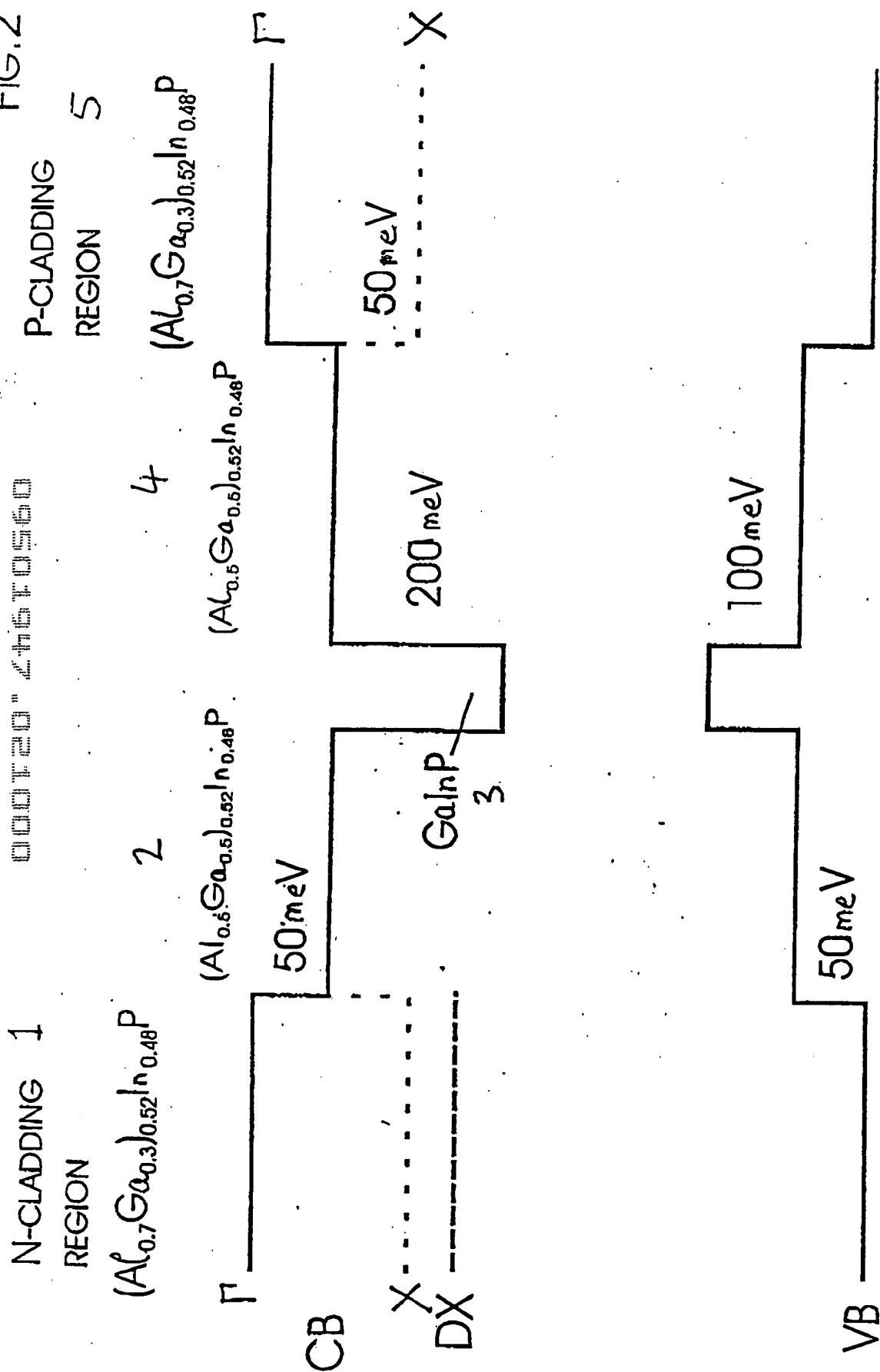
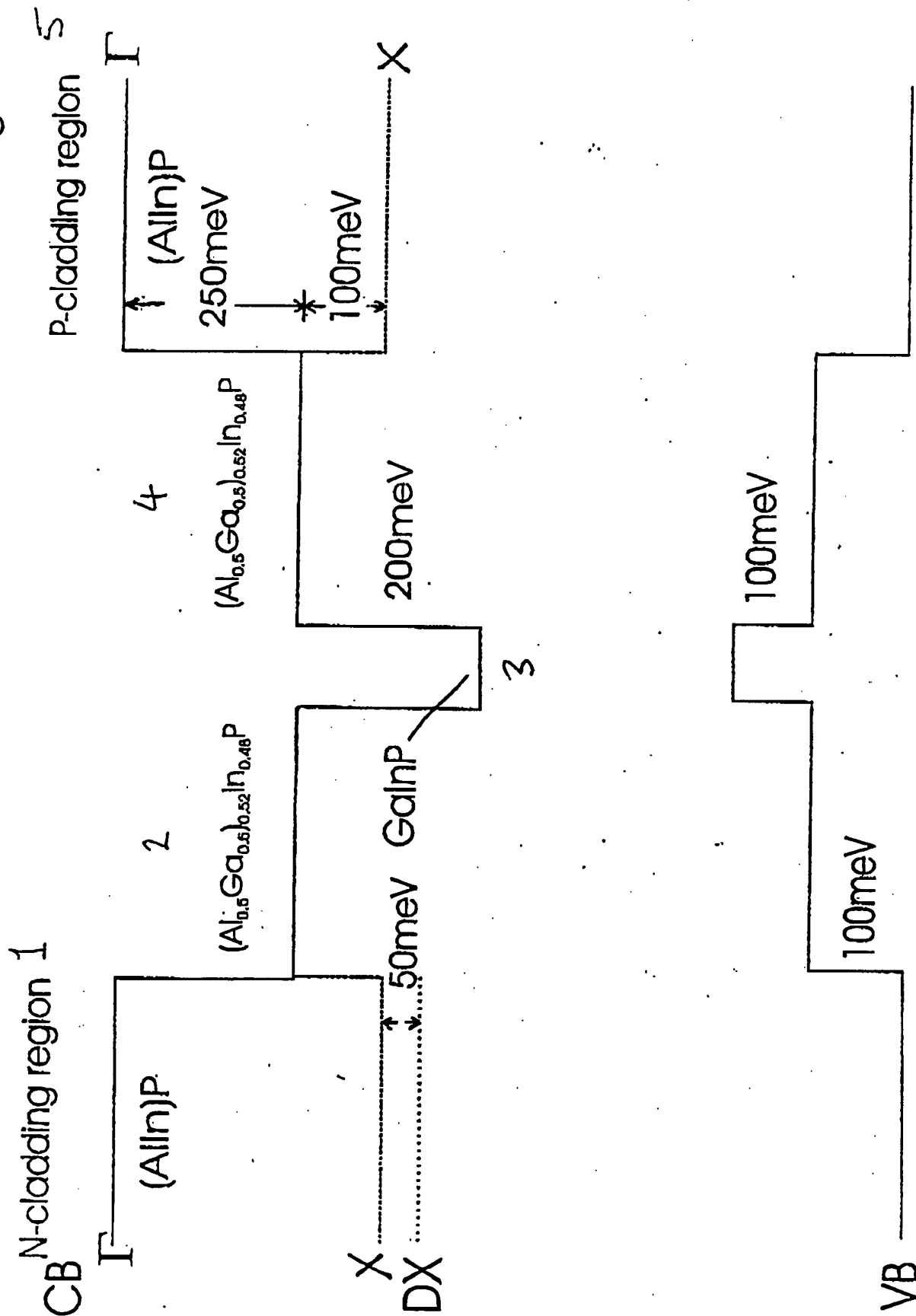


Fig.3



11

N-cladding region

16

AlInP

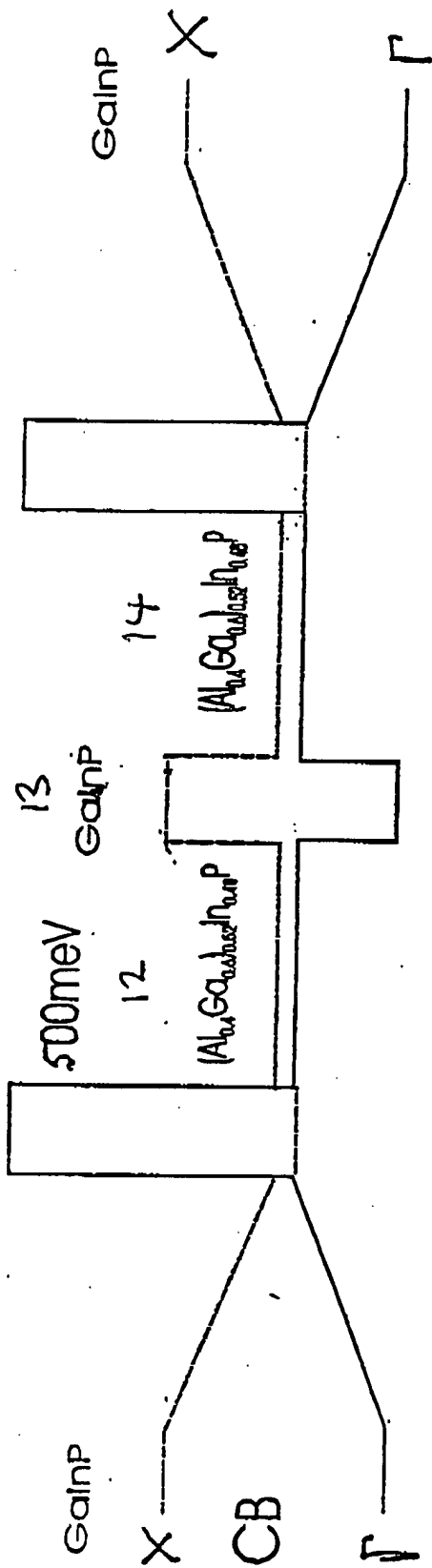
000T20" 246T0560

17

AlInP

P-cladding region

15 Fig.4



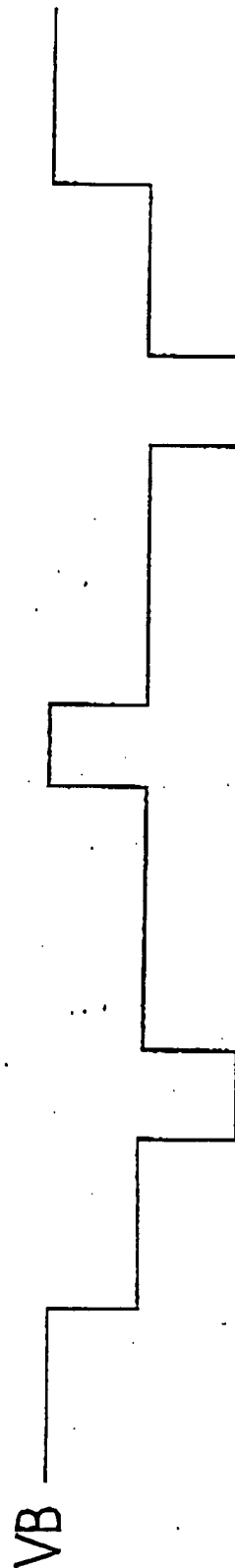
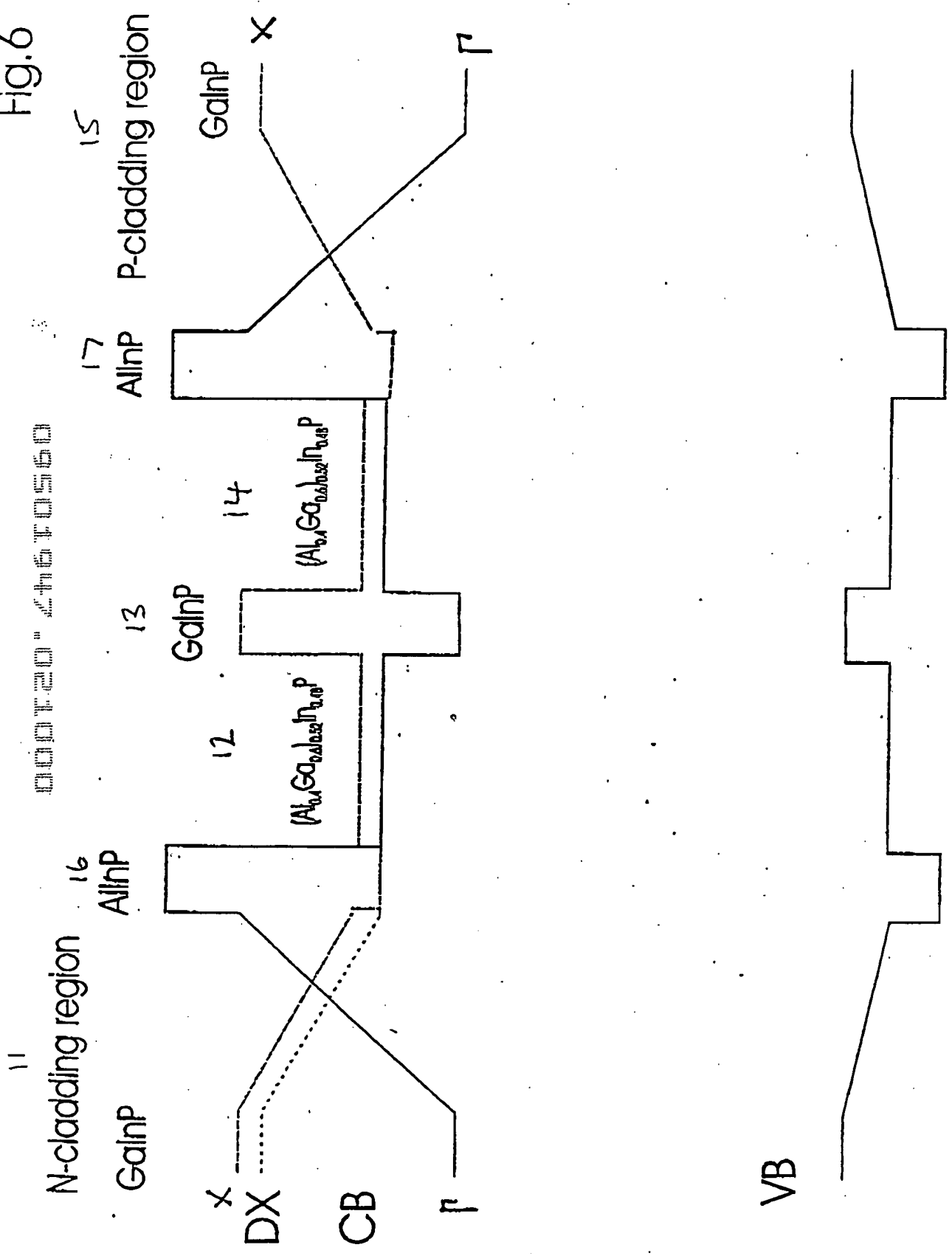
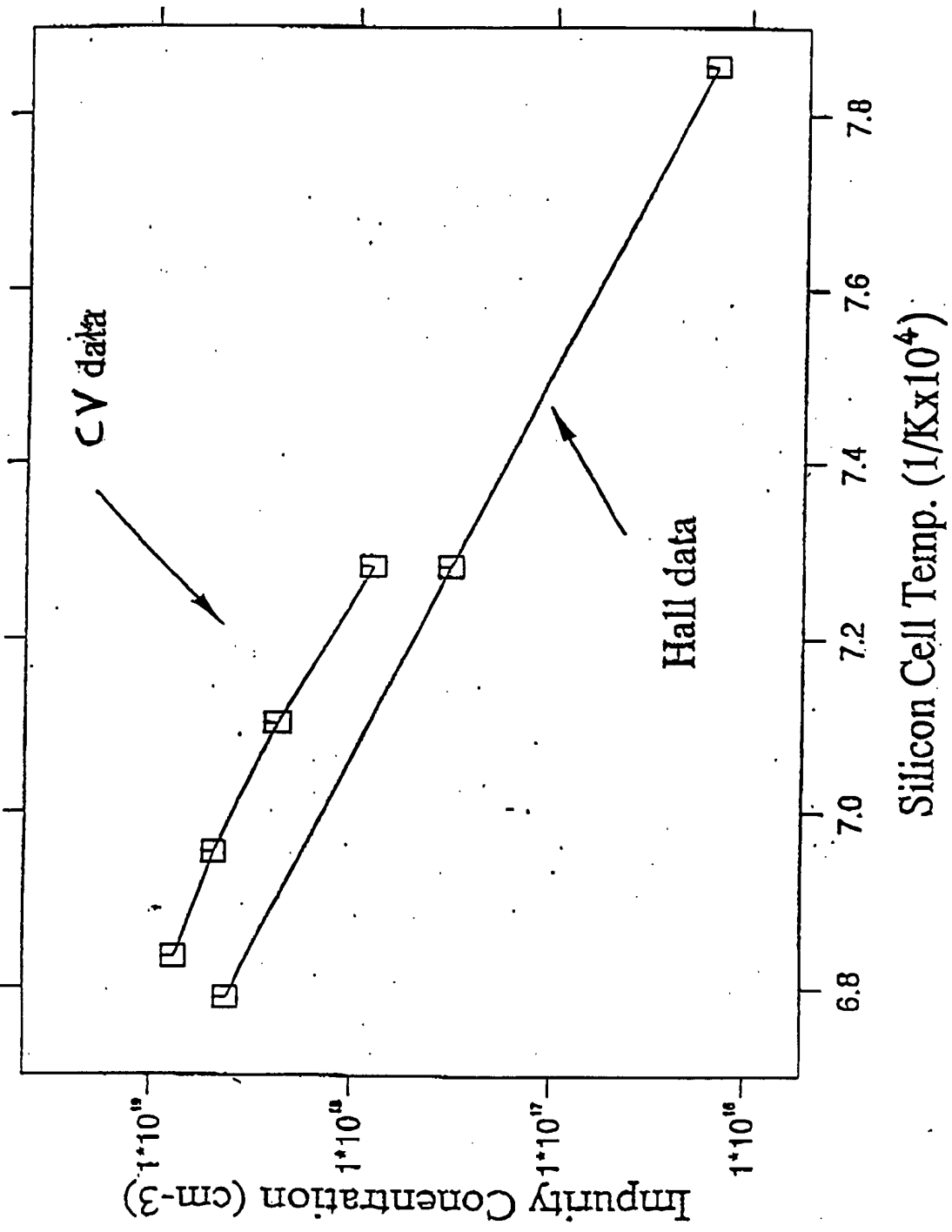


Fig.6

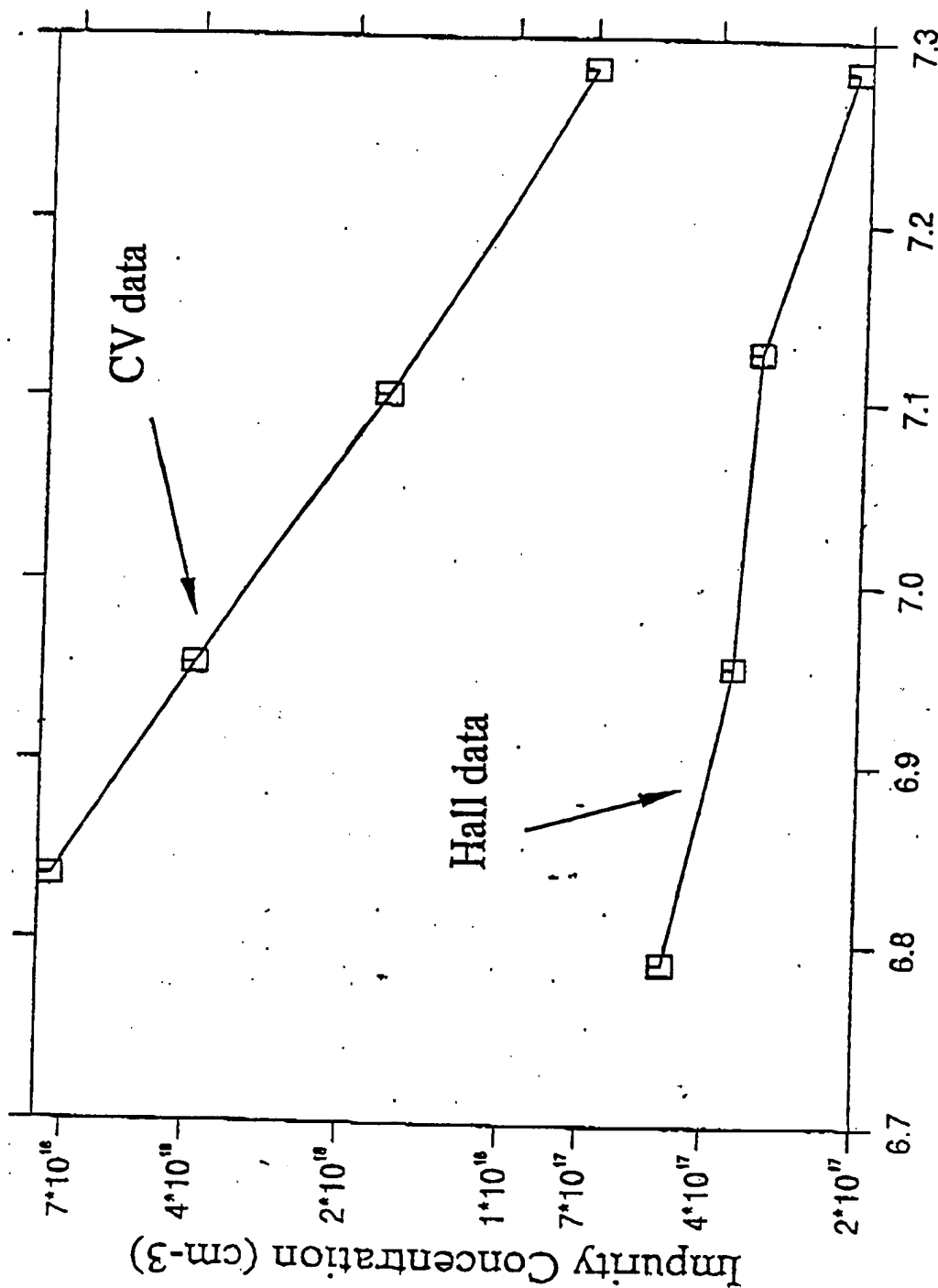


GaInP Silicon Doping



DOTED" 246T050

AlGaInP (y=0.7) Silicon Doping



Silicon Cell Temp.(1/Kx10⁴)

9/17

Fig 9

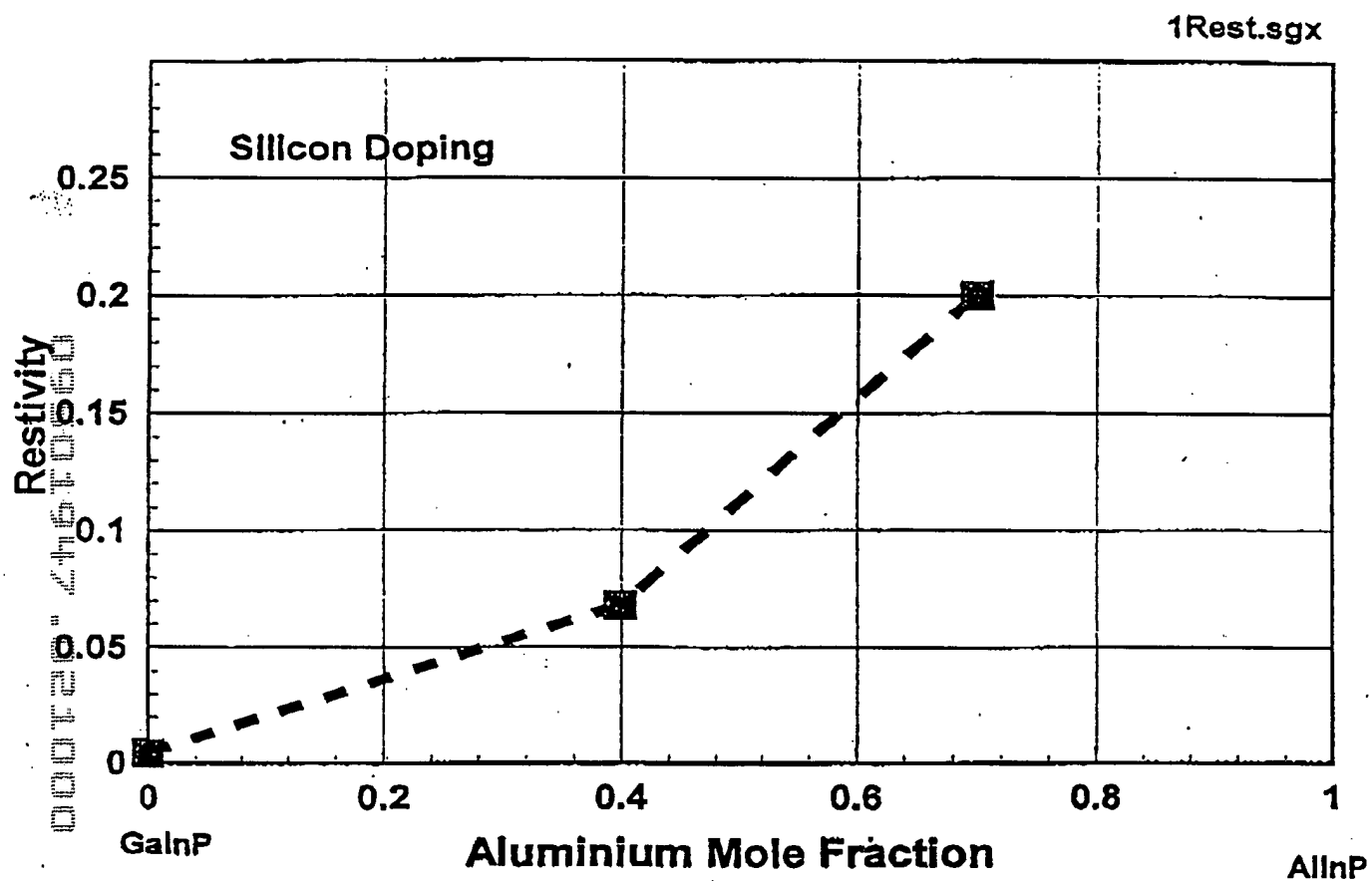


FIG. 9

Figure 10

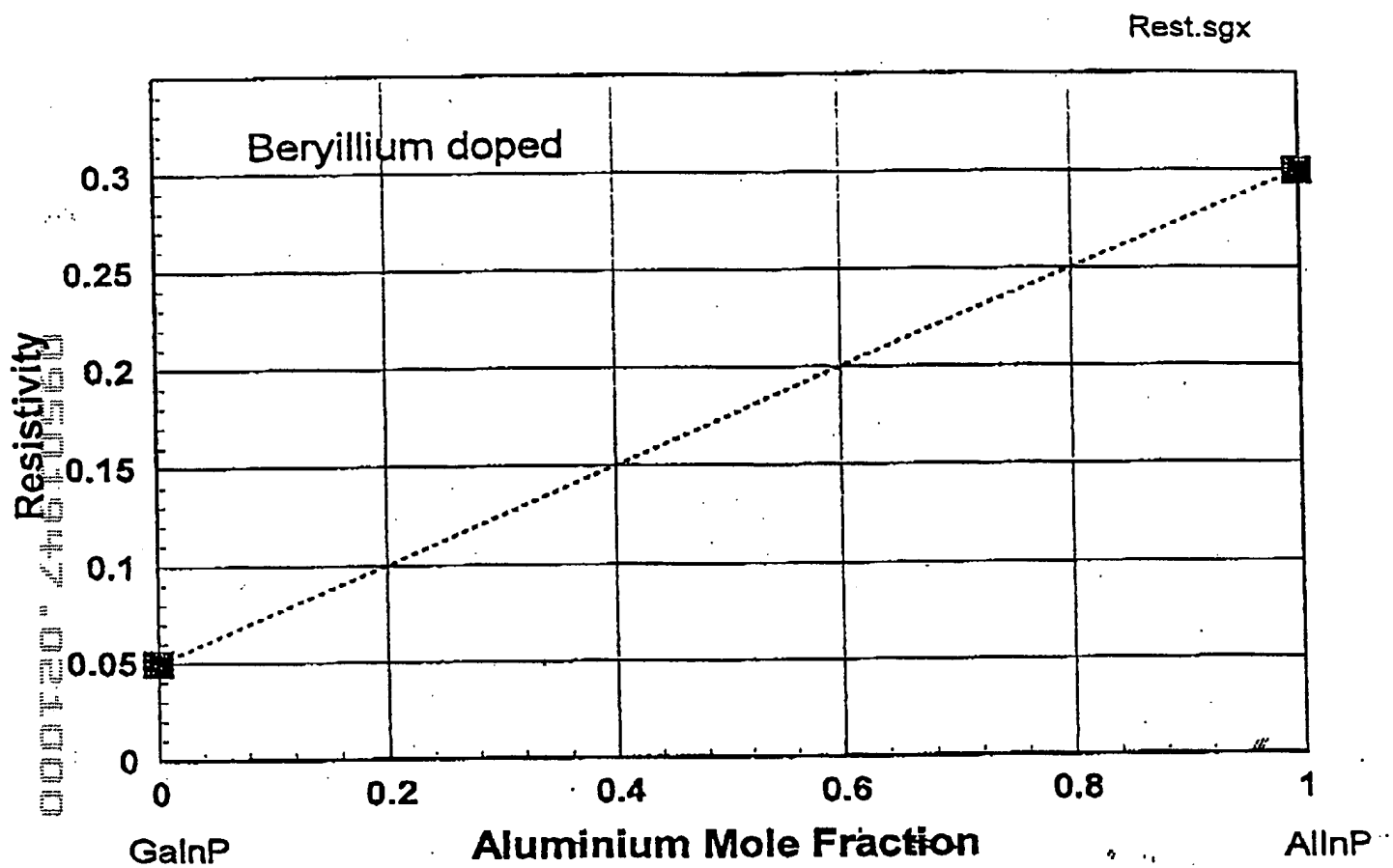
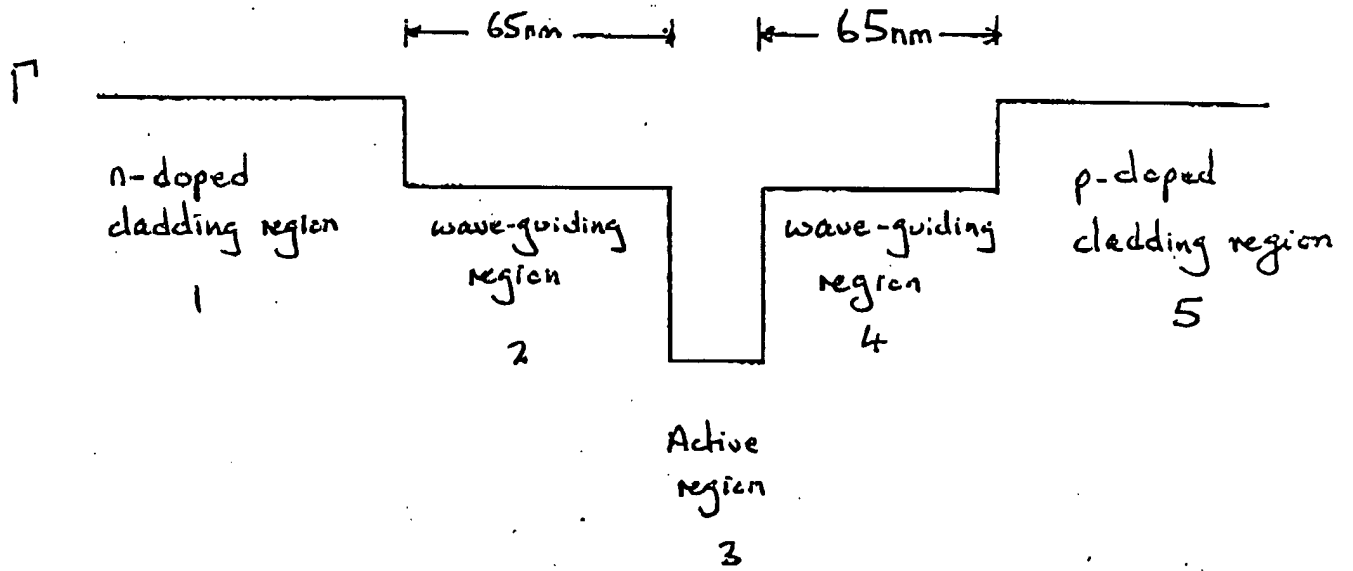


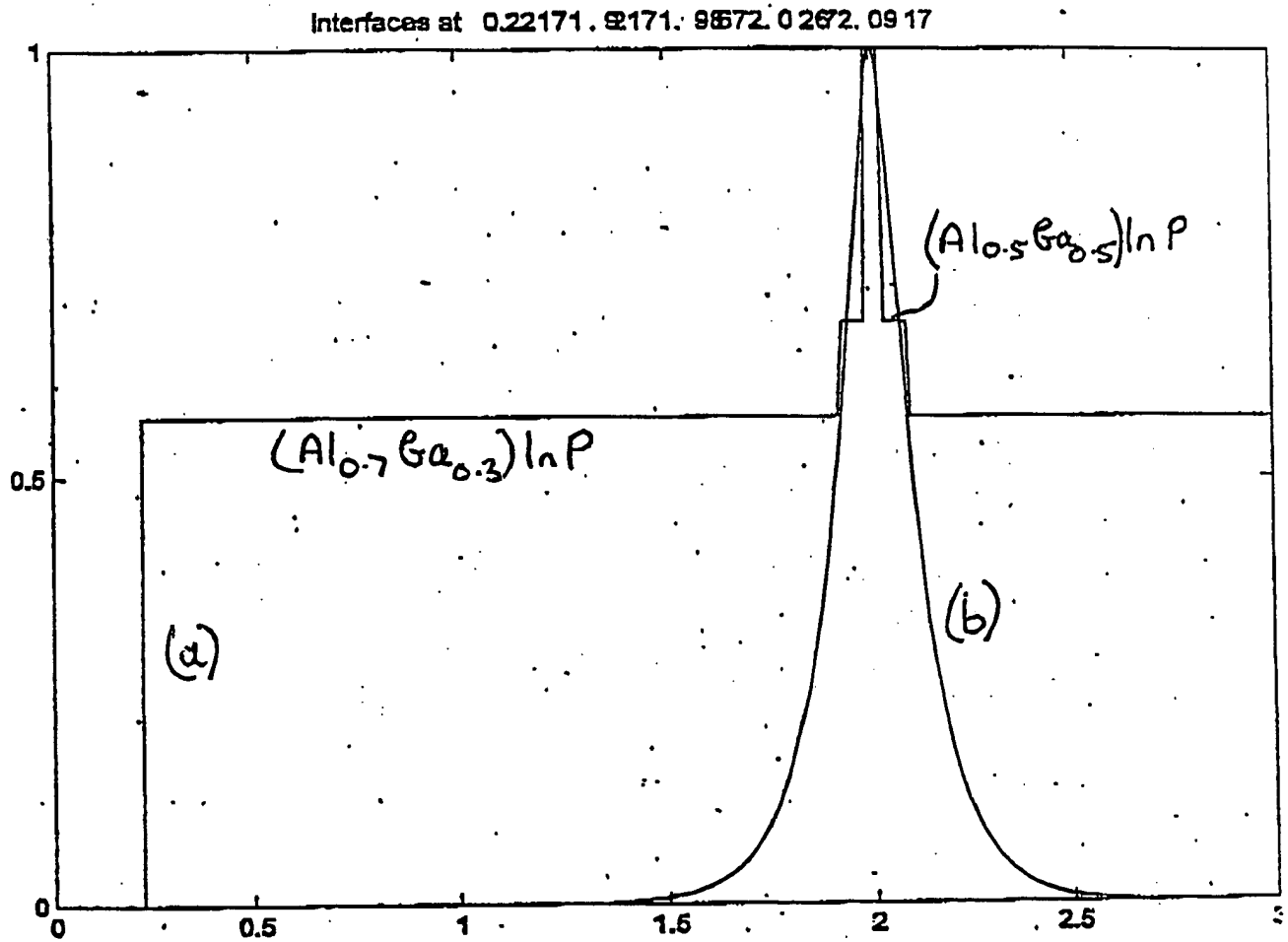
Figure 11 (a)



09501947.021000

12/17

Figure 11 (b)



000120-41610560

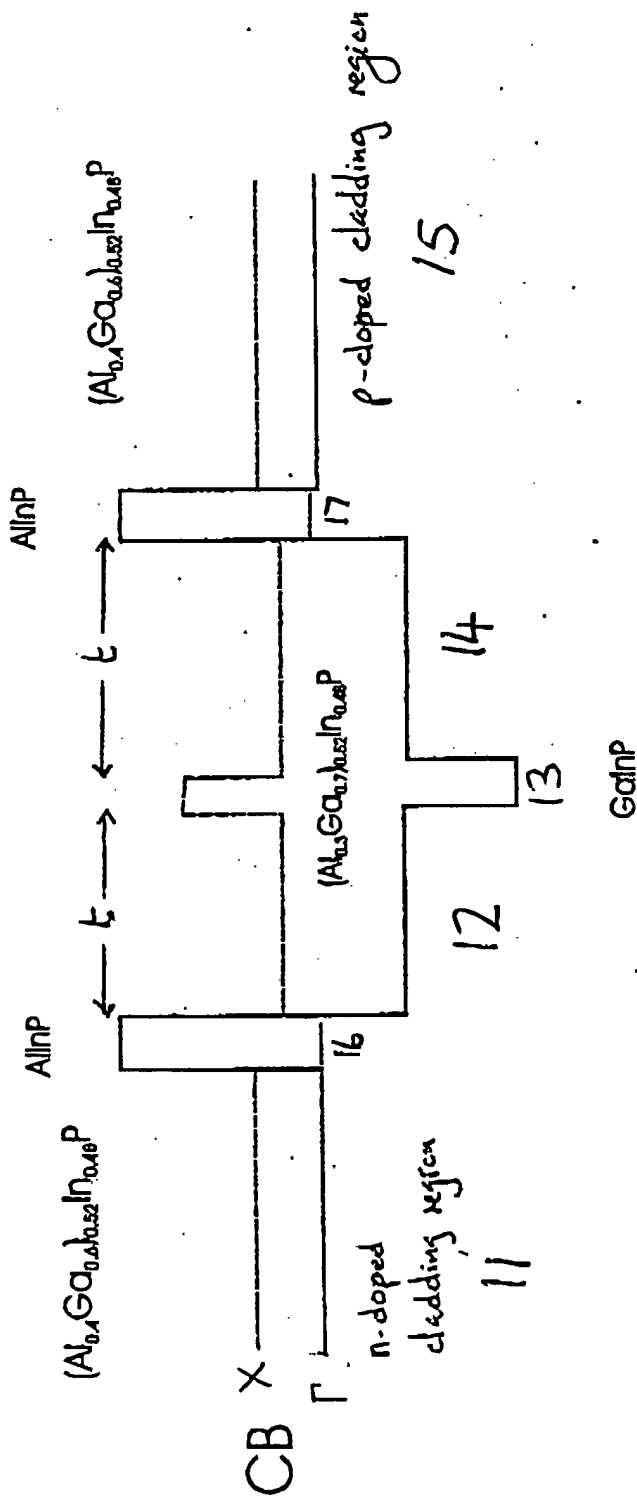
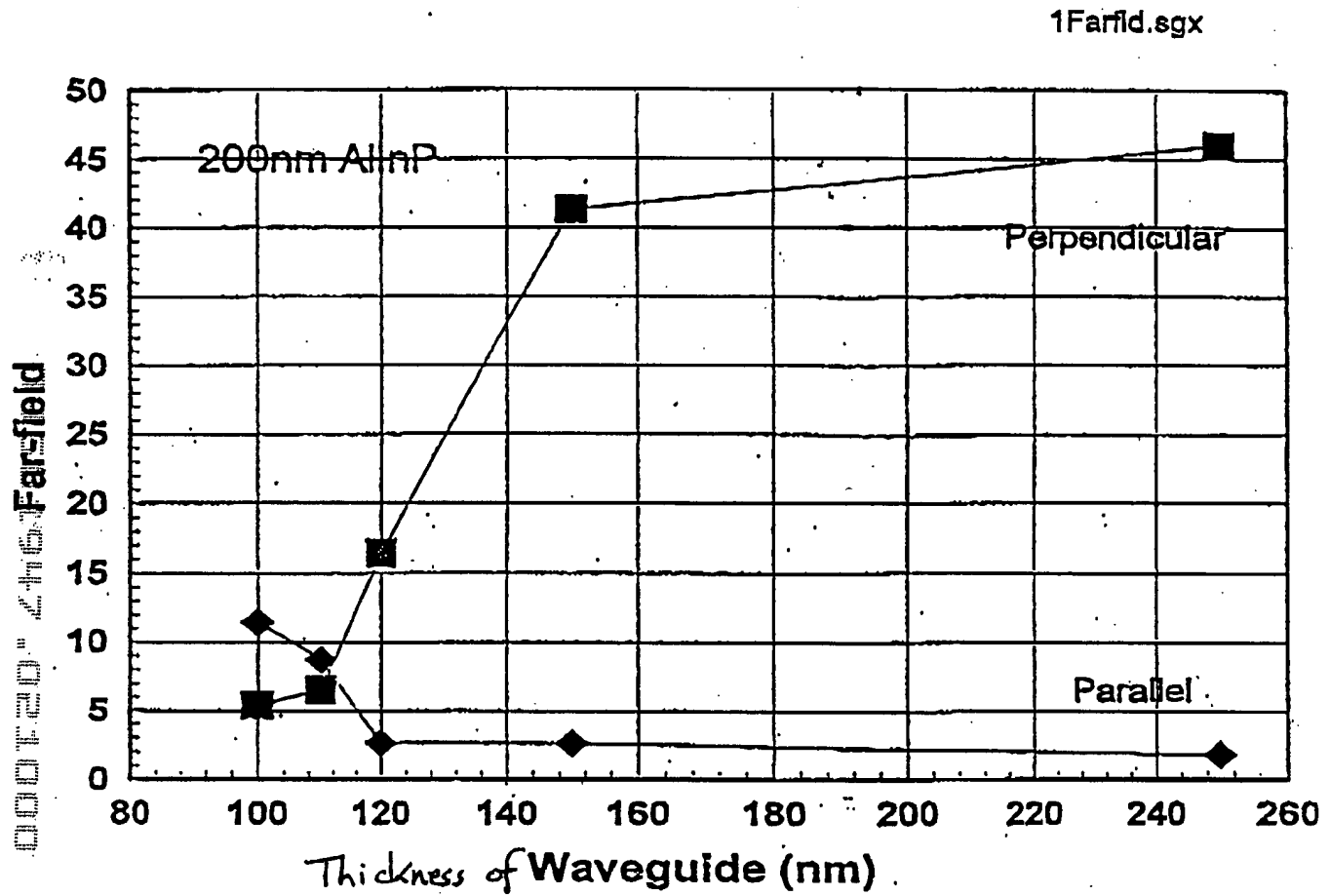


Figure 13(a)



15/17

Figure 13(b)

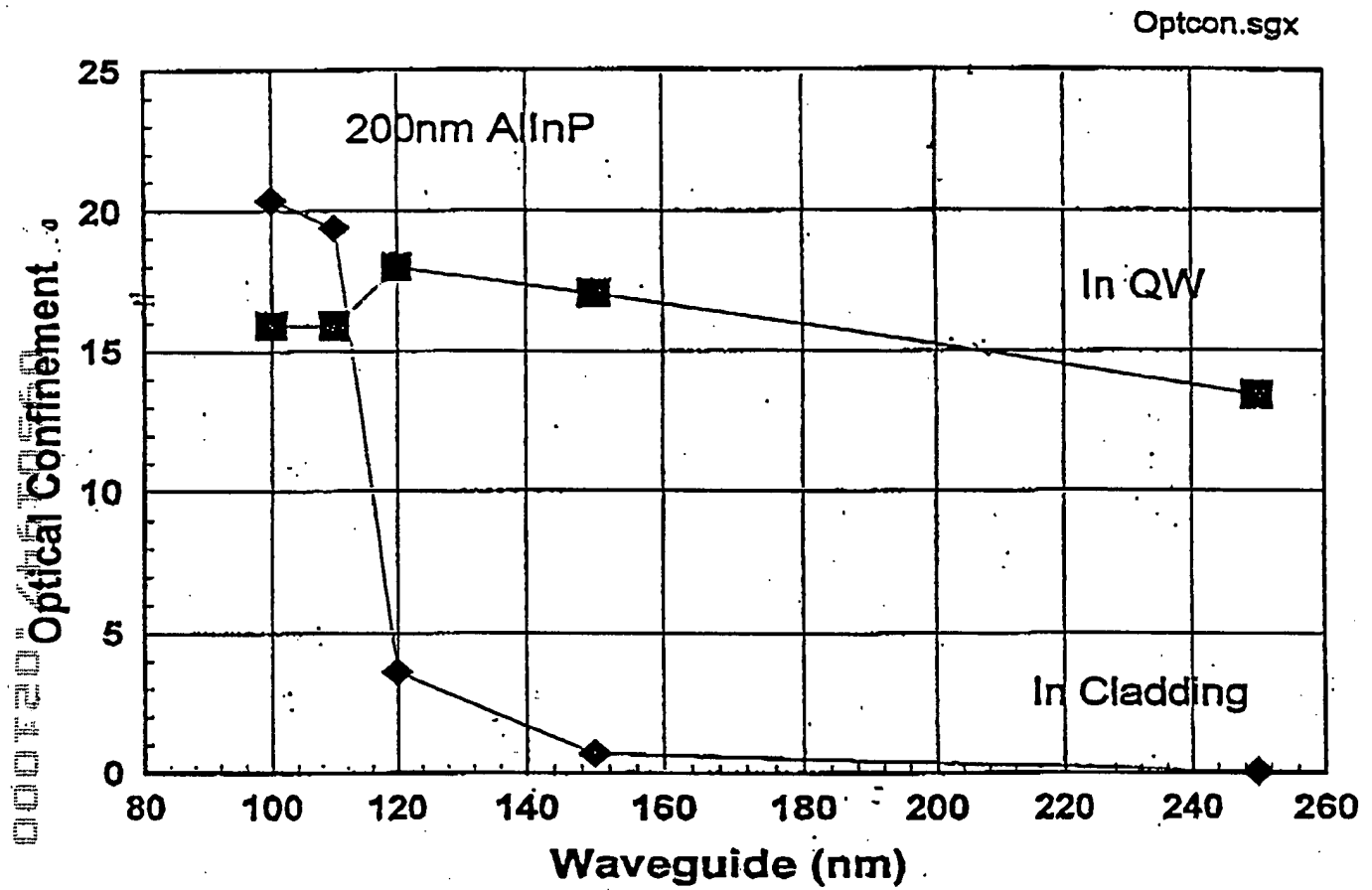


Fig. 13 (b)

Figure 14(a)

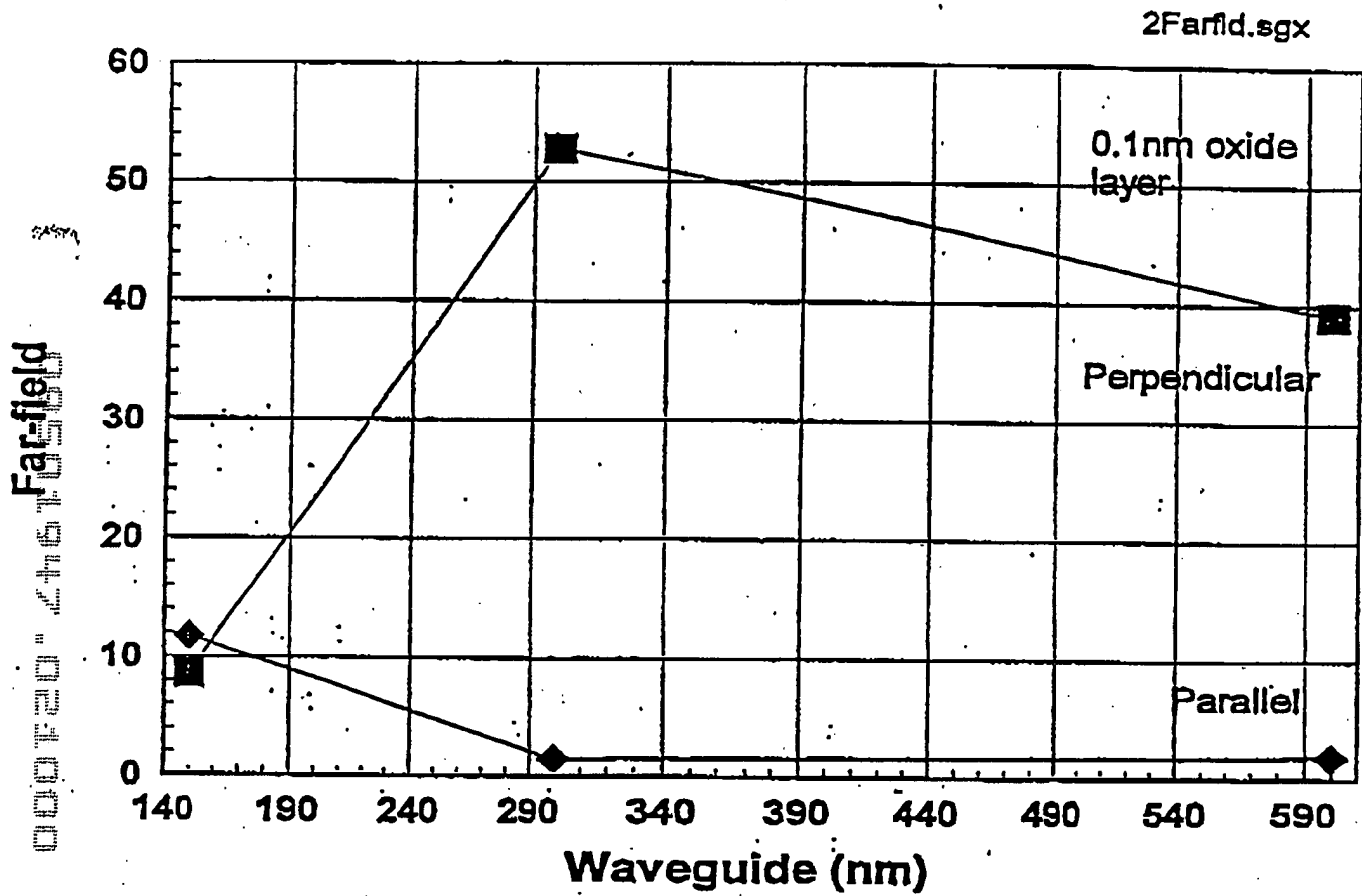


Figure 14(b)

